

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF479** is Designed for 12.5 V FM Large-Signal Amplifier Applications to 50 MHz.

MAXIMUM RATINGS

I_C	2.0 A (CONT)
V_{CE}	18 V
V_{CB}	36 V
P_{DISS}	30 W @ $T_C = 25^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	5.85 $^\circ\text{C}/\text{W}$

PACKAGE STYLE TO-220AB (COMMON EMITTER)				
	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

1 = BASE 2 = EMITTER
3 = COLLECTOR TAB = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20\text{ mA}$	18			V
BV_{CBO}	$I_C = 20\text{ mA}$	36			V
BV_{EBO}	$I_E = 5.0\text{ mA}$	4.0			V
I_{CES}	$V_{CES} = 15\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	30	50		---
C_{ob}	$V_{CB} = 12.5\text{ V}$ $f = 1.0\text{ MHz}$		120	155	pF
G_{PE}	$V_{CC} = 12.5\text{ V}$ $I_{CO} = 20\text{ mA}$ $P_{out} = 15\text{ W (PEP)}$	12	14		dB
η	$f_1 = 30\text{ MHz}$ $f_2 = 30.001\text{ MHz}$	40			%
d_3				-30	dB

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REV. A

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Specifications are subject to change without notice.